

600V N-Channel General Purpose Switching Device Applications

Features

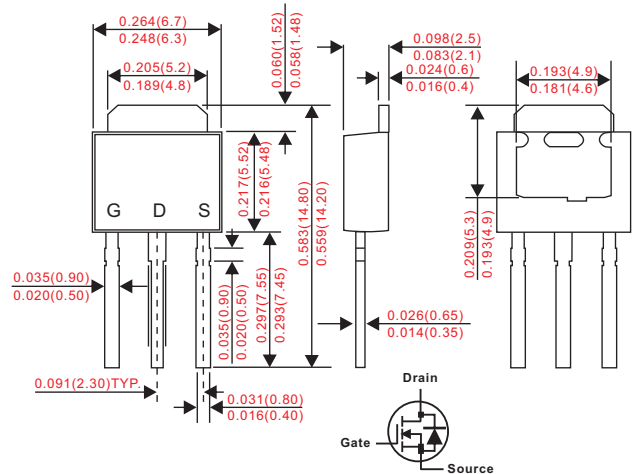
- 600V, 2.0A, $R_{DS(on)} = \text{maximum } 5\Omega @ V_{GS} = 10V$.
- 100% avalanche, EAS tested.
- Suffix "G" indicates Halogen-free part, ex. M02N601D1G.

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : JEDEC TO-251 molded plastic body over passivated chip
- Lead : Axial leads, solderable per MIL-STD-202, Method 208 guaranteed.

Outline

TO-251



Maximum ratings

Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

PARAMETER	CONDITIONS	Symbol	M02N601D1	UNIT
Drain to source voltage		V_{DSS}	600	V
Gate-source voltage		V_{GSS}	±30	
Drain current-continue -pulsed		I_D	2	A
	PW < 10us, duty cycle < 1%	I_{DP}	8	
Allowable power dissipation	$T_c = 25^\circ\text{C}$	P_D	31	W
	Derate above 25°C		0.25	
Channel temperature		T_{CH}	150	°C
Storage thermal		T_{STG}	-55 ~ +150	°C
Avalanche current(2)		I_{AV}	2	A
Avalanche energy(single pulse)(1)		E_{AS}	61	mJ

Note: 1. $V_{DD} = 50V$, $L = 20mH$, $I_{AV} = 2A$, $R_c = 25\Omega$.

2. Repetitive rating : pulse width limited by maximum junction temperature.

600V N-Channel General Purpose Switching Device Applications

■ Electrical characteristics

(AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Drain-to-source breakdown voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	$V_{(BR)DSS}$	600			V
Zero-gate voltage drain current	$V_{DS} = 600\text{V}, V_{GS} = 0\text{V}$	I_{DSS}			10	μA
Gate-to-source leakage current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	I_{GSS}			± 100	nA
Cutoff voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(off)}$	2		4	V
Forward transfer admittance	$V_{DS} = 40\text{V}, I_D = 1.0\text{A}$	$ Y_{fs} $		1.0		S
Static drain-to-source on-state resistance	$I_D = 1.0\text{A}, V_{GS} = 10\text{V}$	$R_{DS(on)}$		4.0	5.0	Ω
Input capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	C_{iss}		356		pF
Output capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	C_{oss}		31		pF
Reverse transfer capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	C_{rss}		4.0		pF
Total gate charge	$V_{DS} = 480\text{V}, I_D = 2.0\text{A}, V_{GS} = 10\text{V}$	Q_G		9.5		nC
Gate source charge		Q_{GS}		2.3		
Gate drain charge		Q_{GD}		4.7		
Turn-on delay time	$V_{GS} = 10\text{V}, V_{DD} = 300\text{V}, I_D = 2.0\text{A}$ $R_{GS} = 25\Omega$	$t_{d(on)}$		11.5		ns
Rise time		t_r		14.3		
Turn-off delay time		$t_{d(off)}$		23		
Fall time		t_f		8.3		
Diode forward voltage	$I_S = 1.0\text{A}, V_{GS} = 0\text{V}$	V_{SD}			1.4	V

Rating and characteristic curves

Fig 1.ON-REGION CHARACTERISTICS

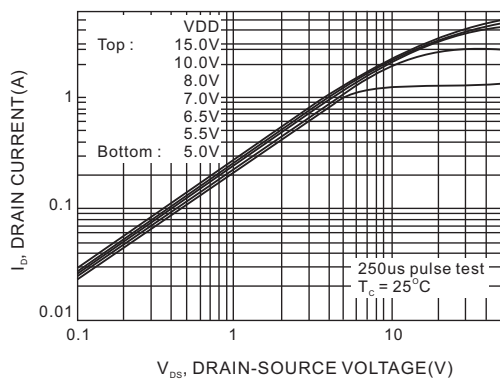


Fig 2.TRANSFER CHARACTERISTICS

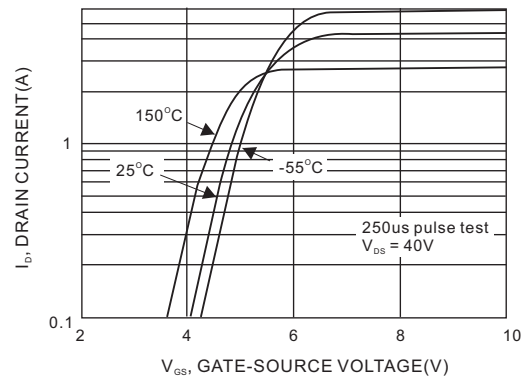


Fig 3.ON-RESISTANCE VARIATION VS DRAIN CURRENT AND GATE VOLTAGE

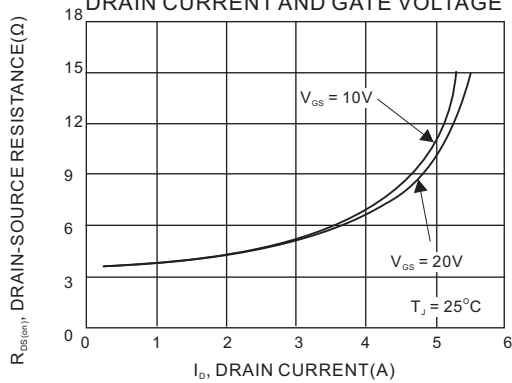


Fig 4.BODY DIODE FORWARD VOLTAGE VARIATION WITH SOURCE CURRENT AND TEMPERATURE

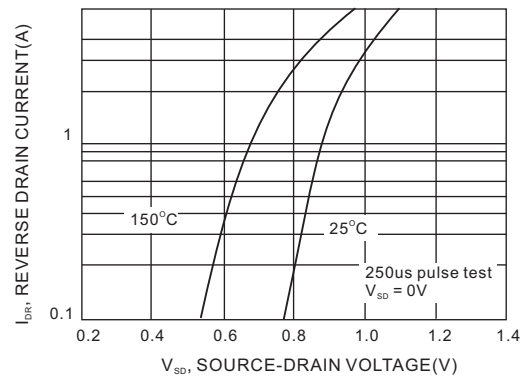


Fig 5.CAPACITANCE CHARACTERISTICS

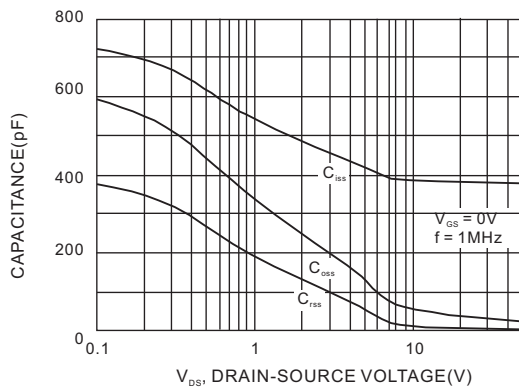
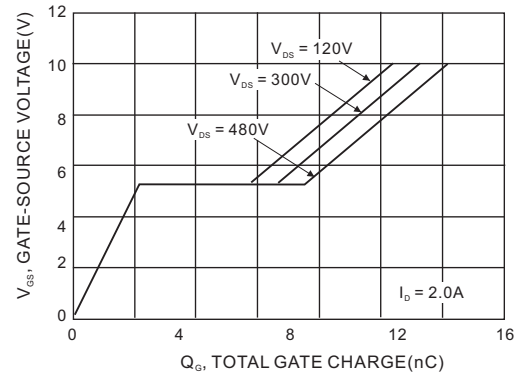


Fig 6.GATE CHARGE CHARACTERISTICS



Rating and characteristic curves

Fig 7. BREAKDOWN VOLTAGE VARIATION VS TEMPERATURE

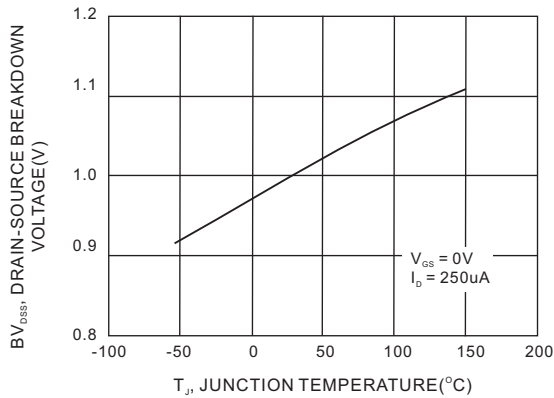


Fig 8. ON-RESISTANCE VARIATION

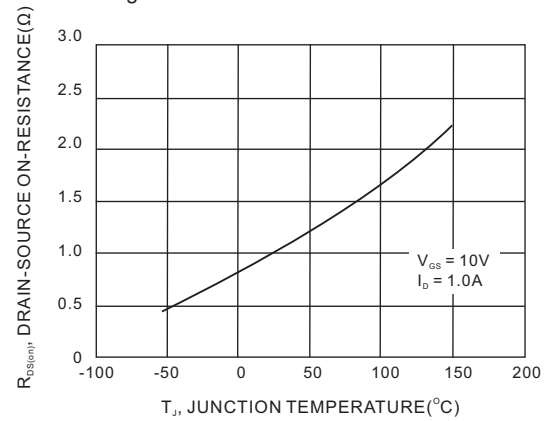


Fig 9. MAXIMUM SAFE OPERATING AREA FOR M02N601D1

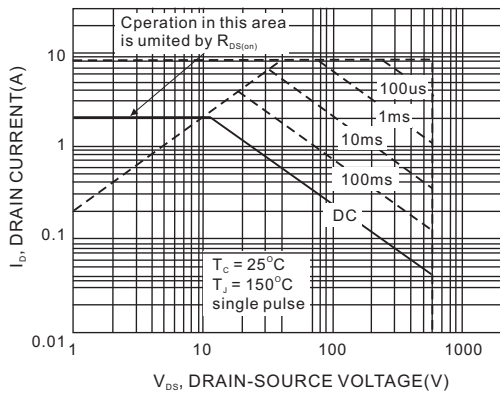


Fig 10. MAXIMUM DRAIN CURRENT VS CASE TEMPERATURE

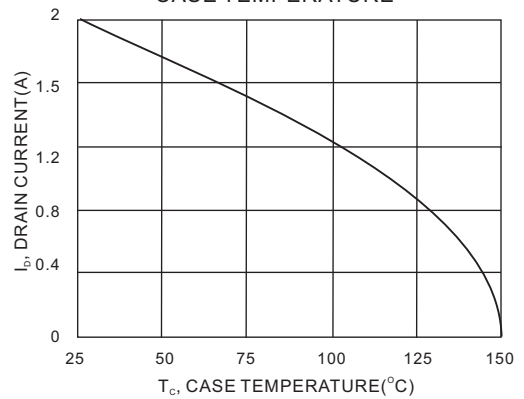
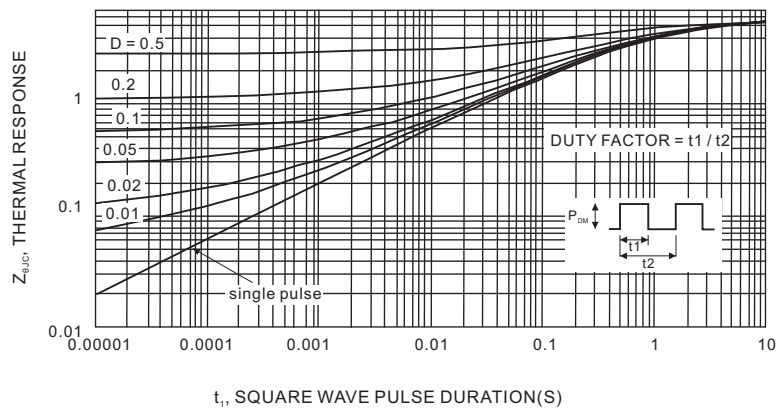


Fig 11. TRANSIENT THERMAL RESPONSE CURVE FOR M02N601D1



- CITC reserves the right to make changes to this document and its products and specifications at any time without notice.
- Customers should obtain and confirm the latest product information and specifications before final design, purchase or use.
- CITC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does CITC assume any liability for application assistance or customer product design.
- CITC does not warrant or accept any liability with products which are purchased or used for any unintended or unauthorized application.
- No license is granted by implication or otherwise under any intellectual property rights of CITC.
- CITC products are not authorized for use as critical components in life support devices or systems without express written approval of CITC.